

Form PTO-1449

Applicant: Toshiki Makimoto, et al.
 Serial No.: 10/516,380
 Filing Date: November 30, 2004
 For: P-TYPE NITRIDE SEMICONDUCTOR STRUCTURE AND BIPOLAR TRANSISTOR



Sheet 1 of 3
 Confirmation No.: 2860
 Att'y Docket No.: 14321.63
 Art Unit: 2818

INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANT

U.S. Patent Documents

Examiner Initial*	Document Number	Issue Date	Name
THN 1	2002/0146855 A1	10/10/2002	Goto et al.

Foreign Patent Documents

Examiner Initial*	Document Number	Publication Date	Country or Patent Office	Translation
THN 2	5-175225	7/13/1993	Japan	No
THN 3	5-291282	11/5/1993	Japan	No
THN 4	7-245316	9/19/1995	Japan	No
THN 5	2003-007998	1/10/2003	Japan	No
THN 6	2002-305204	10/18/2002	Japan	No
THN 7	10-065216	03/06/2002	Japan	No
THN 8	11-150296	06/02/1999	Japan	No

Other Documents

(including author, title, pertinent pages, etc.)

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THN 9 K. Kumakura, T. Makimoto and N. Kobayashi, *Low-Resistance Nonalloyed Ohmic Contact to p-type GaN Using Strained InGa_N Contact Layer*, Applied Physics Letters, Vol. 79, No. 16, pp 2588-2590 (2001).

Examiner:

Date Considered:

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12/16/2006

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

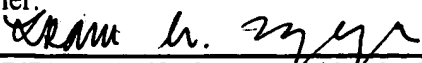
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- THN 10 T. Makimoto, et al., *Reduced Damage Of Electron Cyclotron Resonance Etching By In Doping Into p-GaN*, Journal of Crystal Growth 221, pp. 350-355 (2000).
- THN 11 T. Makimoto, et al., *High Current Gains Obtained by InGaN/GaN Double Heterojunction Bipolar Transistors*, phys. stat. sol. (a) 188, No. 1, pp. 183-186, (2001).
- THN 12 L.S. McCarthy, et al., *AlGaIn/GaN Heterojunction Bipolar Transistor*, IEEE Electron Device Letters, Vol. 20, No. 6, pp. 277-270 (1999).
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- THN 14 K.P. Lee, et al., *Self-Aligned Process for Emitter- and Base-Regrowth GaN HBTs and BJTs*, Solid-State Electronics 45, pp. 243-247 (2001),
- THN 15 T. Makimoto et al., *High Current Gain of 3000 for GaN/InGaIn HBTs with a Regrown Base Layer*, Technical Report of IEICE. ED2003-25 CPM2003-24 SDM2003-25 (2003-5), pp. 49-52.
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- THN 17 T. Makimoto et al., *High Current Gain (>2000) and Reduced Common-emitter Offset Voltage of GaN/InGaIn Double Heterojunction Bipolar Transistors*, Conference Digest of 61st Device Research Conference, pp. 23-24, June 23-25, 2003.
- THN 18 T. Makimoto et al., *High Current Gain (>2000) of GaN/InGaIn double Heterojunction Bipolar Transistors Using Base Regrowth of p-InGaIn*, Applied Physics Letters, Vol. 83, No. 5, pp. 1035-1037 (2003).

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